

L Number	Hits	Search Text	DB	Time stamp
1	0	(led or (light adj emitting adj diode)) and (plated adj recess) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:33
2	3	(led or (light adj emitting adj diode)) and (plated adj recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:15
3	21	(plated adj recess) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:22
4	2	(ellipsoidal adj dome) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:26
5	0	(elliptical adj encapsulant) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:24
6	0	(ellipsoidal adj encapsulant) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:26
7	20	(led or (light adj emitting adj diode)) and (vias adj through adj substrate) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:58
8	87	(package) and (vias adj through adj substrate) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:43
9	40	(package) and (vias adj through adj substrate) and recess	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:43
10	308	(led or (light adj emitting adj diode)) and (package) and recess and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/05 14:59

L Number	Hits	Search Text	DB	Time stamp
1	0	(first adj second adj interconnections)	USPAT;	2002/11/03 09:01
2	144	with (substrate adj surface) with led	US-PGPUB	
3	0	led with ((metallic or metal) adj layer)	USPAT;	2002/11/03 10:09
4	0	encapsulant adj size adj substrate	US-PGPUB	
5	0	encapsulant adj length adj substrate	USPAT;	2002/11/03 10:10
6	0	encapsulant with (length adj substrate)	US-PGPUB	
-	1	encapsulant with (width adj substrate)	USPAT;	2002/11/03 10:10
-	0	("(semiconductor adj laser) and iiiv").PN.	US-PGPUB	
-	0	("(semiconductor adj laser) and (iii adj	USPAT;	2002/11/02 11:17
-	0	v)").PN.	US-PGPUB	
-	0	("(semiconductor adj laser) and	USPAT;	2002/11/02 11:17
-	9	gallium").PN.	US-PGPUB	
-	0	(semiconductor adj laser) and iiiv	USPAT;	2002/11/02 11:18
-	0	((semiconductor adj laser) and iiiv) and	US-PGPUB	
-	3	(edge adj emitter)	USPAT;	2002/11/02 11:21
-	1	((semiconductor adj laser) and iiiv) and	US-PGPUB	
-	1	edge	USPAT;	2002/11/02 13:30
-	1	6069440.pn.	US-PGPUB	
-	1	6045240.pn.	USPAT;	2002/11/02 13:30
-	18	encapsulated adj light adj emitting adj	US-PGPUB	
-	0	diode	USPAT;	2002/11/02 13:37
-	0	(encapsulated adj light adj emitting adj	US-PGPUB	
-	0	diode) with transparent	USPAT;	2002/11/02 13:41
-	0	(transparent adj encapsulated adj	US-PGPUB	
-	0	material) adj substrate	USPAT;	2002/11/02 13:39
-	87	transparent adj encapsulated adj material	US-PGPUB	
-	17	transparent adj encapsulat\$	USPAT;	2002/11/02 13:41
-		(transparent adj encapsulat\$) and led	US-PGPUB	
-			USPAT;	2002/11/02 13:42
-			US-PGPUB	
-			USPAT;	2002/11/02 13:43
-			US-PGPUB	
-			USPAT;	2002/11/03 08:58
-			US-PGPUB	